

Silicon PNP Power Transistors

2SB886

DESCRIPTION

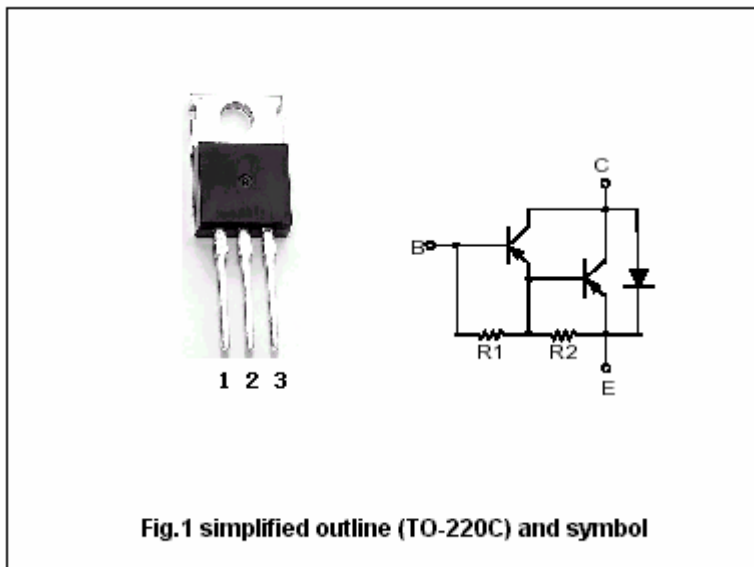
- With TO-220C package
- Complement to type 2SD1196
- DARLINGTON
- High DC current gain
- High current capacity and wide ASO
- Low saturation voltage

APPLICATIONS

- Motor drivers, printer
- Hammer drivers
- Relay drivers,
- Voltage regulator control.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-110	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current (DC)		-8	A
I_{CM}	Collector current-Peak		-12	A
P_C	Collector dissipation	$T_C=25^{\circ}\text{C}$	40	W
			1.75	
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-50~150	$^{\circ}\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA$; $R_{BE}=\infty$	-100			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-5mA$; $I_E=0$	-110			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-4A$; $I_B=-8mA$		-1.0	-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-4A$; $I_B=-8mA$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-80V$; $I_E=0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V$; $I_C=0$			-3.0	mA
f_T	Transition frequency	$I_C=-4A$; $V_{CE}=-5V$		20		MHz
h_{FE}	DC current gain	$I_C=-4A$; $V_{CE}=-3V$	1500	4000		

Switching times

t_{on}	Turn-on time	$I_C=-4A$; $I_{B1}=-I_{B2}=-8mA$ $R_L=12.5\Omega$, Duty cycle $\leq 1\%$ $V_{CC}=50V$		0.7		μs
t_{stg}	Storage time			1.4		μs
t_f	Fall time			1.5		μs

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PACKAGE OUTLINE

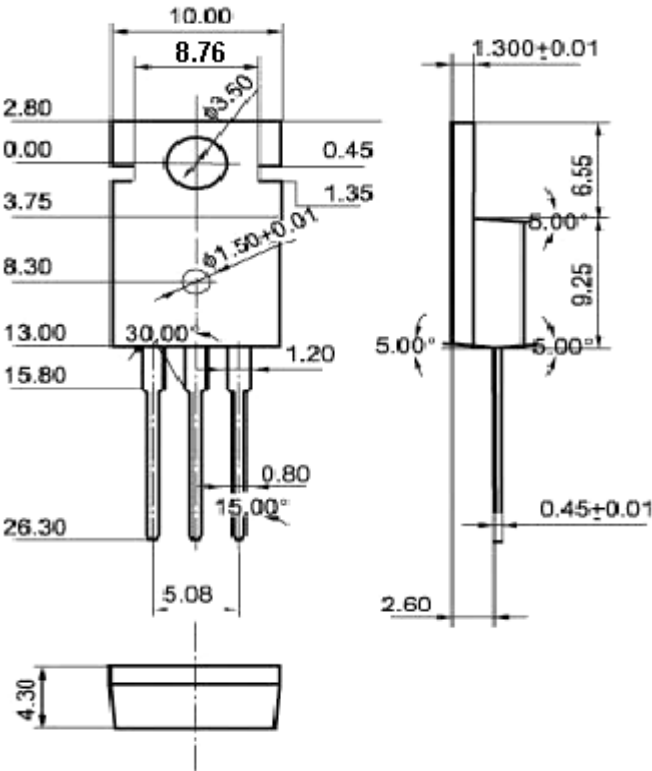


Fig.2 Outline dimensions (unindicated tolerance: $\pm 0.10\text{mm}$)